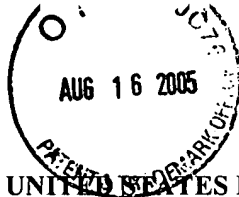


Docket No.: 057454-0979



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
Hideto HIDAKA	:	Confirmation Number: 7421
Application No.: 10/691,513	:	Group Art Unit: 2827
Filed: October 24, 2003	:	Examiner: LE, THONG Q.

For: THIN FILM MAGNETIC MEMORY DEVICE FOR PROGRAMMING REQUIRED INFORMATION WITH AN ELEMENT SIMILAR TO A MEMORY CELL AND INFORMATION PROGRAMMING METHOD

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

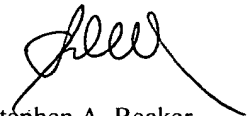
This Information Disclosure Statement is being filed under Rule 37 CFR 1.97(i), wherein applicants are submitting references before the grant of a patent to be placed in the file.

Accordingly, copies of the references as listed on the attached Form PTO-1449 are submitted herewith for placement in the file. A copy of the corresponding foreign application office action, together with and English language version thereof, is also attached for the Examiner's information. No certification or fees are deemed necessary.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

McDERMOTT WILL & EMERY LLP


Stephen A. Becker
Registration No. 26,527

600 13th Street, N.W.
Washington, DC 20005-3096
Phone: 202.756.8000 SAB:slh
Facsimile: 202.756.8087
Date: August 16, 2005

Please recognize our Customer No. 20277 as our correspondence address.



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 057454-0979		SERIAL NO. 10/691,513	
				APPLICANT Hideto HIDAKA			
				FILING DATE October 24, 2003		GROUP 2827	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US 2002/0009003 A1	01/24/2002	Hartmann	Corresponds to DE 100 34062 A1		
		US 6,646,911 B2	11/11/2003	Hidaka	Corresponds to DE 102 28 560 A1		
		US 5,751,627	05/12/1998	Ooishi			
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number 4 - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No	
		WO 99/53499	10/21/1999	HONEYWELL, INC		X	
		EP 1 132 924 A2	10/11/2000	HEWLETT-PACKARD COMPANY, A DELAWARE CORPORATION		X	
		EP 1 253 651 A2	10/30/2002	KABUSHIKI KAISHA TOSHIBA TOKYO		X	
		DE 100 34062 A1	01/24/2002	INFINEON TECHNOLOGIES AG	Corresponds to USP 2002/0009003 A1		X
		EP 1 189 239 A2	09/14/2001	HEWLETT-PACKARD COMPANY		X	
		DE 102 28 560 A1	05/15/2003	MITSUBISHI DENKI K.K.	Corresponds to USP 6,646,911 B2		X
		WO 01/54279 A1	07/26/2001	PAGEANT TECHNOLOGIES		X	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		Scheuerlein, R., et al. "A 10ns read and write non-volatile memory array using a magnetic tunnel junction and FET switch in each cell" IEEE International Solid-State Circuits Conference, February 7-9, 2000, pp 128-129.					
		Durlam, M., et al. "Nonvolatile RAM based on magnetic tunnel junction elements" IEEE International Solid-State Circuits Conference, February 7-9, 2000, pp 130-131.					
		Naji, P., et al. "A 256kb 3.0V 1T1MTJ nonvolatile magnetoresistive RAM" IEEE International Solid-State Circuits Conference, February 7-9, 2001, pp 122-123, 438.					
		Wee, J., et al. "An antifuse EPROM circuitry scheme for field-programmable repair in DRAM" IEEE Journal of Solid-State Circuits, Vol. 35, No. 10, October 2000, pp 1408-1414.					
		Black, W., et al. "Programmable logic using giant-magnetoresistance and spin-dependent tunneling devices (invited)" Journal of Applied Physics, Vol. 87, No. 9, May 2000, pp 6647-6679.					
EXAMINER				DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.